



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



企业微信二维码



企业QQ二维码

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C
60V	20mΩ @ V _{GS} = 10V	36.3A
	27mΩ @ V _{GS} = 4.5V	31.2A

Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R_{DS(ON)} – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Wettable Flank for Improved Optical Inspection
- ESD Protected Gate

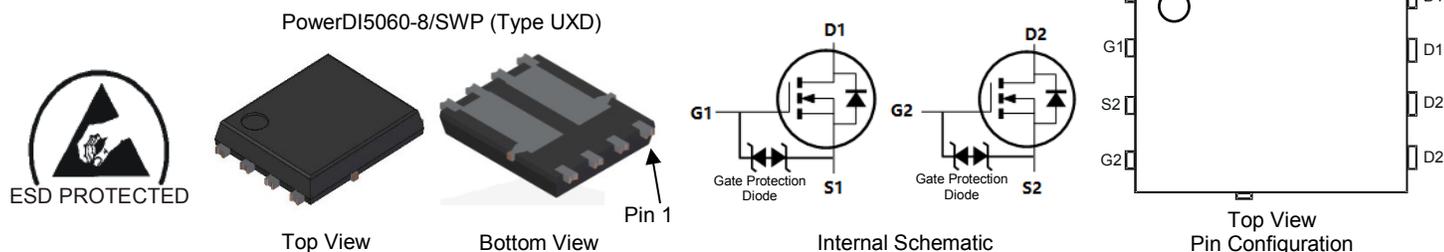
Description and Applications

This new generation N-channel enhancement mode MOSFET is designed to minimize R_{DS(ON)} yet maintain superior switching performance. This device is ideal for use in power management and load switch.

- Wireless Charging
- DC-DC Converters
- Power Management

Mechanical Data

- Case: PowerDI[®] 5060-8
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Lead-Frame; Solderable per MIL-STD-202, Method 208 ^{Ⓔ3}
- Weight: 0.097 grams (Approximate)



Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	± 16	V
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 6)	I_D	$T_C = +25^\circ\text{C}$	36.3
		$T_C = +100^\circ\text{C}$	25.6
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 5)	Steady State I_D	$T_A = +25^\circ\text{C}$	9.4
		$T_A = +100^\circ\text{C}$	6.6
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	140	A
Maximum Continuous Body Diode Forward Current (Note 5)	I_S	35	A
Pulsed Body Diode Forward Current (10 μs Pulse, Duty Cycle = 1%)	I_{SM}	140	A
Avalanche Current $L = 0.1\text{mH}$	I_{AS}	20.4	A
Avalanche Energy $L = 0.1\text{mH}$	E_{AS}	20.8	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	57	$^\circ\text{C}/\text{W}$
Total Power Dissipation (Note 6)	P_D	39.5	W
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	3.8	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 48\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.3	—	2.5	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	14.3	20	m Ω	$V_{GS} = 10\text{V}, I_D = 10\text{A}$
		—	19.2	27		$V_{GS} = 4.5\text{V}, I_D = 6\text{A}$
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	$V_{GS} = 0\text{V}, I_S = 1\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	825	—	pF	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	244	—		
Reverse Transfer Capacitance	C_{rss}	—	20.5	—		
Gate Resistance	R_G	—	1.5	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	7.1	—	nC	$V_{DS} = 30\text{V}, I_D = 10\text{A}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	14.3	—		
Gate-Source Charge	Q_{gs}	—	2.1	—		
Gate-Drain Charge	Q_{gd}	—	2.8	—		
Turn-On Delay Time	$t_{D(ON)}$	—	4.0	—	ns	$V_{GS} = 10\text{V}, V_{DS} = 30\text{V}, R_G = 6\Omega, I_D = 10\text{A}$
Turn-On Rise Time	t_R	—	5.3	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	18.5	—		
Turn-Off Fall Time	t_F	—	8.0	—		
Reverse Recovery Time	t_{RR}	—	22.7	—	ns	$I_F = 6\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge	Q_{RR}	—	12.8	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz. copper, with thermal bias to bottom layer 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

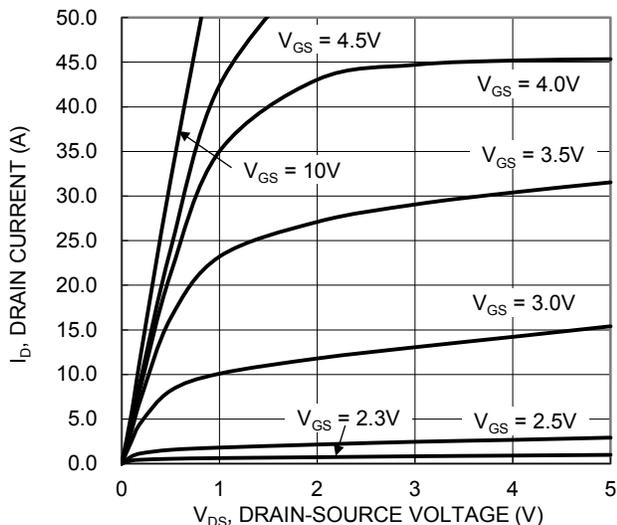


Figure 1. Typical Output Characteristic

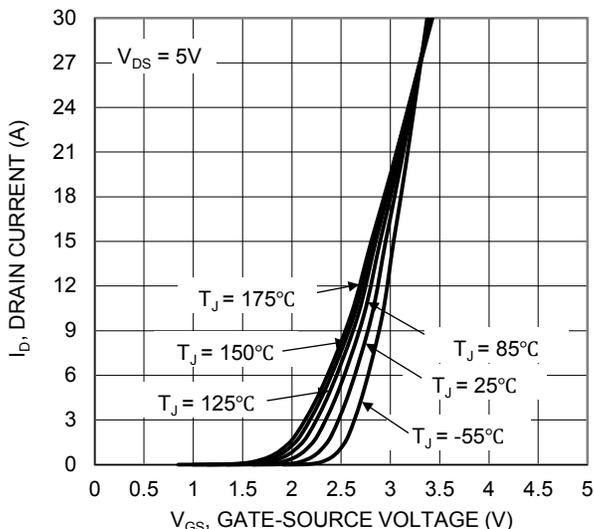


Figure 2. Typical Transfer Characteristic

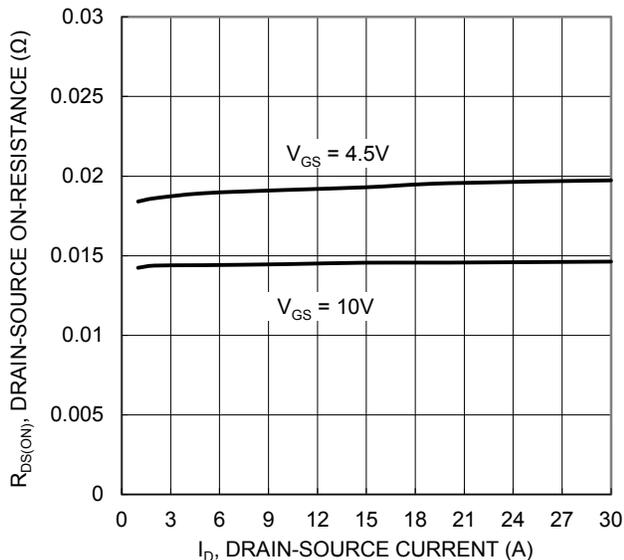


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

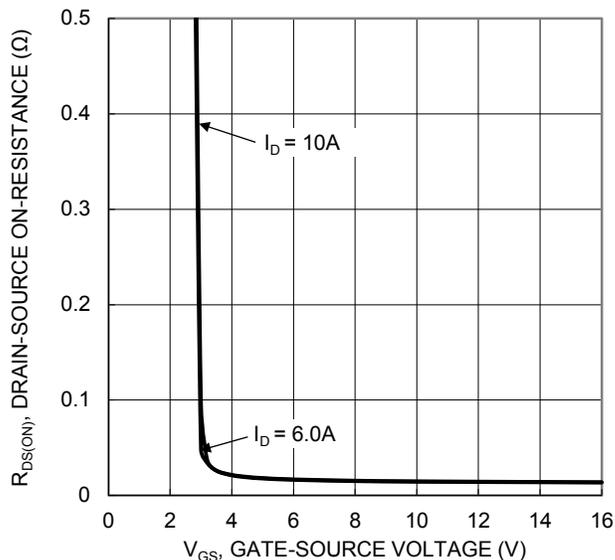


Figure 4. Typical Transfer Characteristic

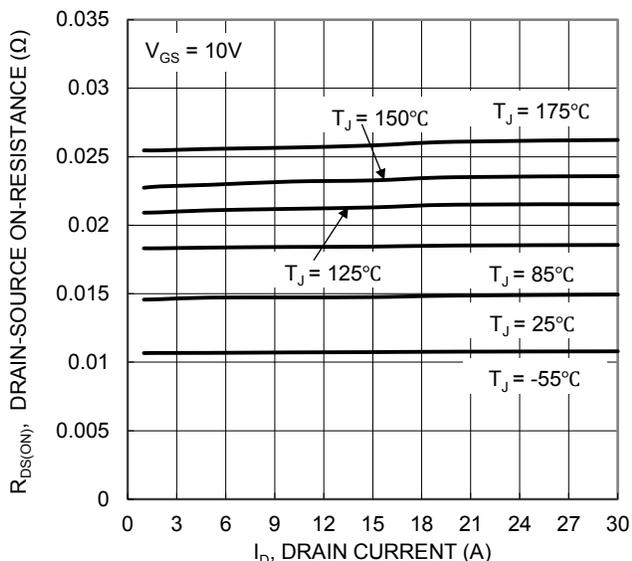


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

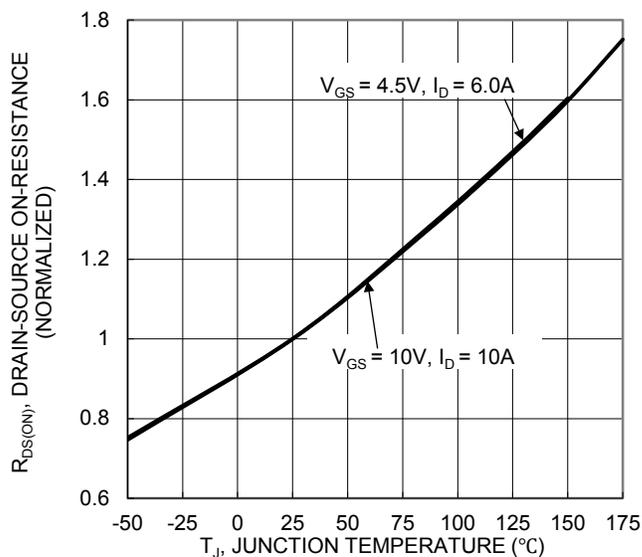


Figure 6. On-Resistance Variation with Junction Temperature

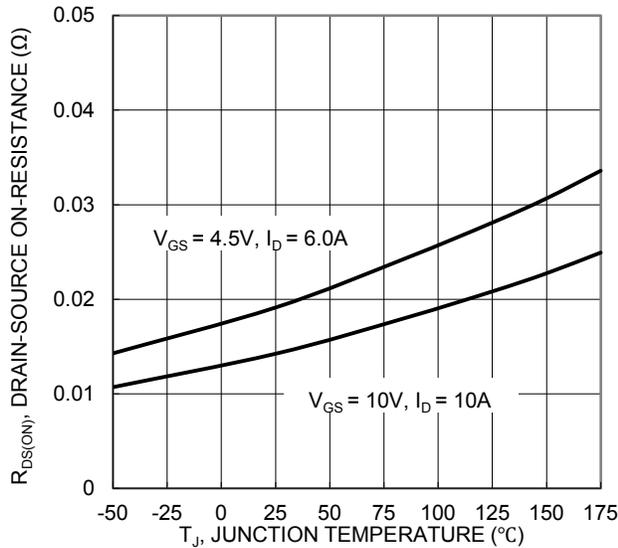


Figure 7. On-Resistance Variation with Junction Temperature

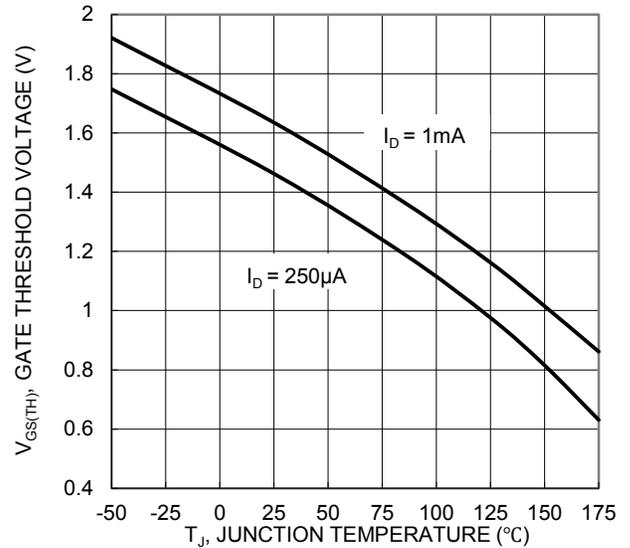


Figure 8. Gate Threshold Variation vs. Junction Temperature

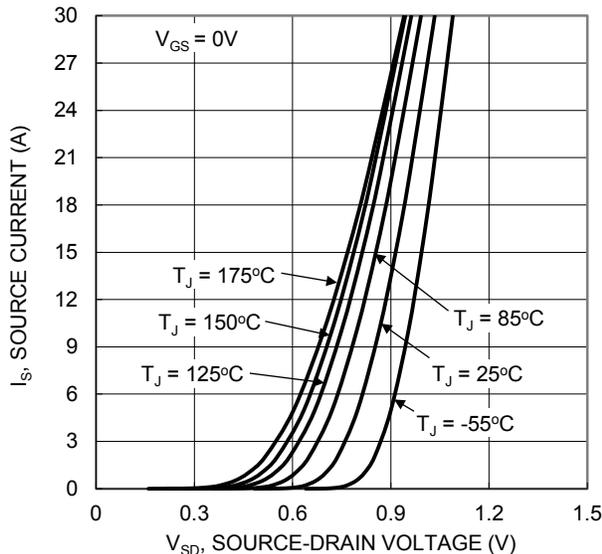


Figure 9. Diode Forward Voltage vs. Current

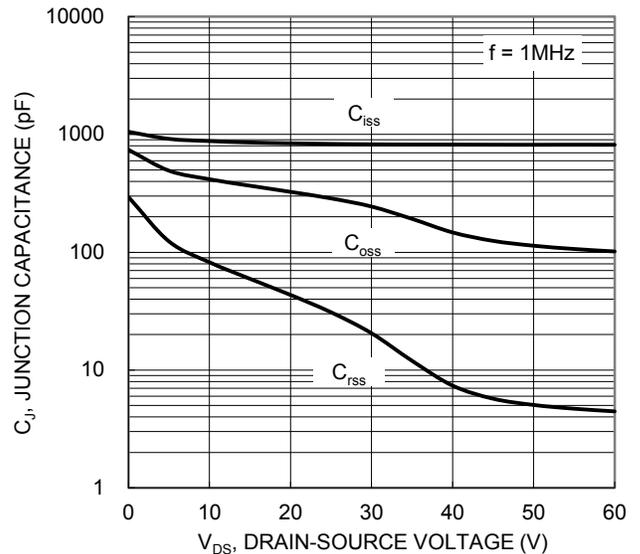


Figure 10. Typical Junction Capacitance

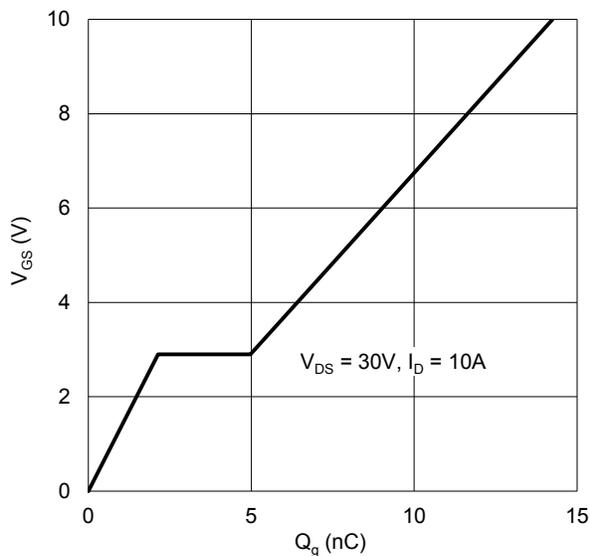


Figure 11. Gate Charge

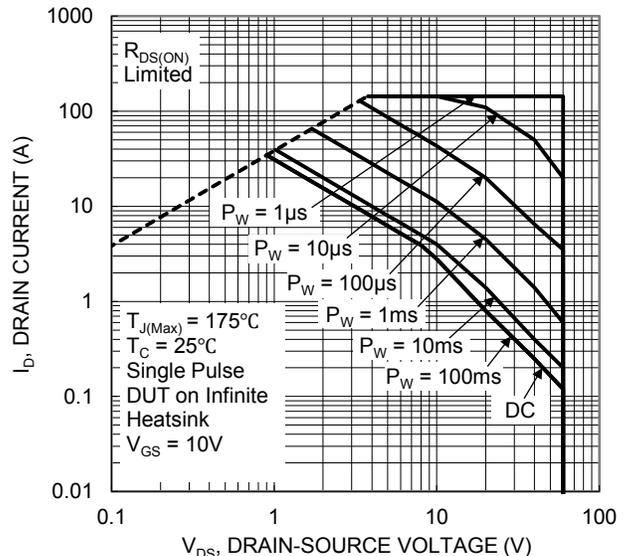


Figure 12. SOA, Safe Operation Area

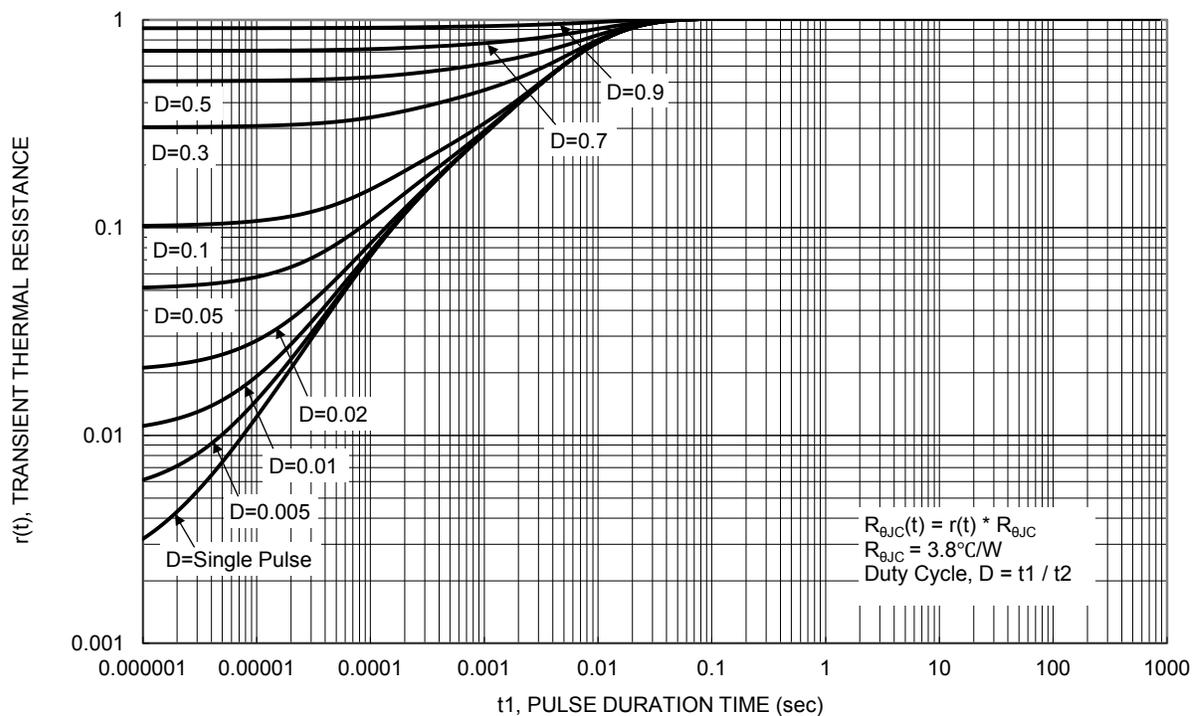
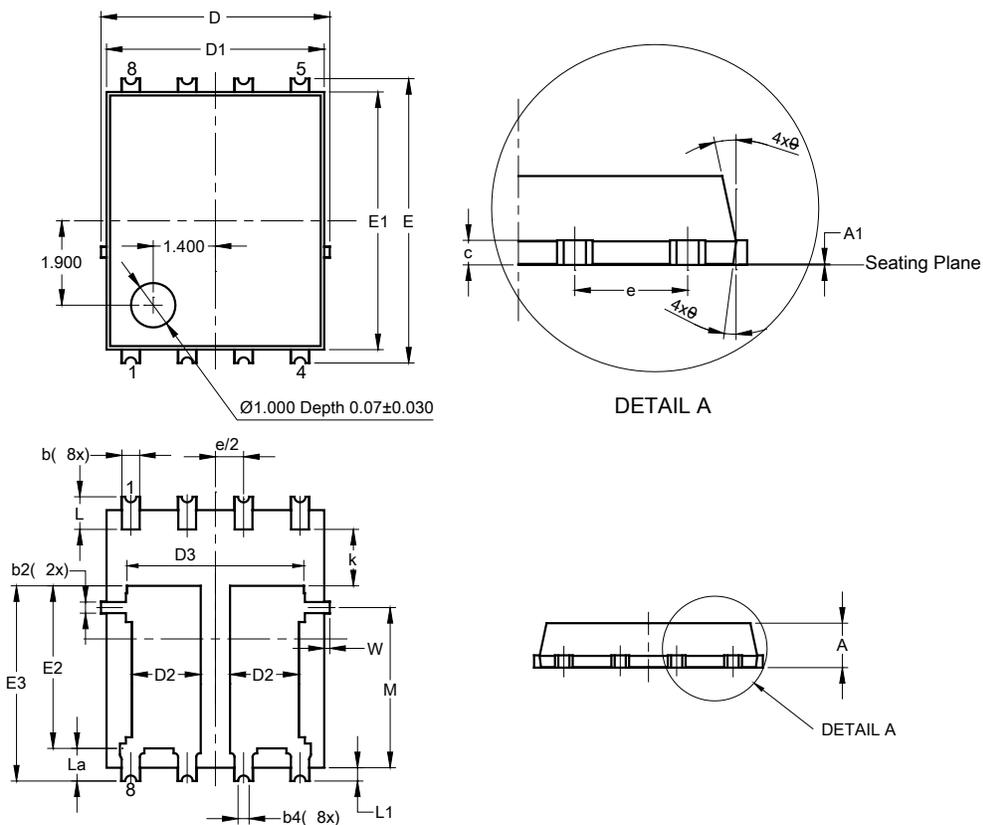


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

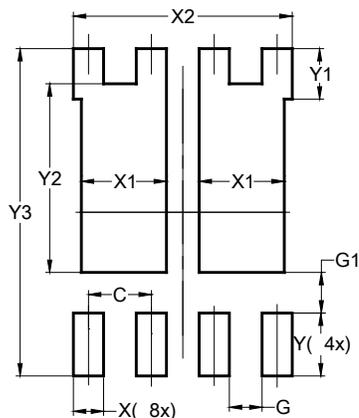
PowerDI5060-8/SWP (Type UXD)



PowerDI5060-8/SWP (Type UXD)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	1.46	1.66	1.55
D3	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
M	3.205	4.005	3.605
W	0.025	0.225	0.125
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

PowerDI5060-8/SWP (Type UXD)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	1.720
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610